

Rev 4, 27-Feb-14

ActivePSRTM Quasi-Resonant PWM Controller

FEATURES

- Patented Primary Side Regulation Technology
- Quasi-Resonant Operation
- Adjustable up to 120kHz Switching Frequency
- +/-5% Output Voltage Regulation
- Accurate OCP/OLP Protection
- Integrated Output Cord Compensation
- Integrated Line and Primary Inductance Compensation
- Built-in Soft-Start Circuit
- Line Under-Voltage, Thermal, Output Overvoltage, Output Short Protections
- Current Sense Resistor Short Protection
- Transformer Short Winding Protection
- Less than 100mW Standby Power
- Complies with Global Energy Efficiency and CEC Average Efficiency Standards
- Tiny SOT23-6 Packages

APPLICATIONS

- AC/DC Adaptors/Chargers for ADSL, PDAs, E-books
- Adaptors for Portable Media Player, DSCs, and Other

GENERAL DESCRIPTION

The ACT411 is a high performance peak current mode PWM controller which applies $ActivePSR^{TM}$ and $ActiveQR^{TM}$ technology. ACT411 achieves accurate voltage regulation without the need of an opto-coupler or reference device.

The ACT411 is designed to achieve less than 100mW Standby Power. By applying frequency fold back and $ActiveQR^{TM}$ technology, ACT411 exceeds the latest ES2.0 efficiency standard.

ACT411 integrates comprehensive protection. In case of over temperature, over voltage, short winding, short current sense resistor, open loop

-1-

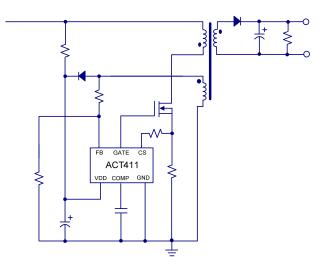
and overload conditions, it would enter auto restart mode including cycle-by-cycle current limiting.

ACT411 is to achieve no overshoot and very short rise time even with big capacitive load ($4000\mu F$) with the built-in fast and soft start process, .

The Quasi-Resonant (QR) operation mode can effectively improve efficiency, reduce the EMI noise and further reduce the components in input filter.

ACT411 is idea for application up to 36 Watt.

Figure 1: Simplified Application Circuit

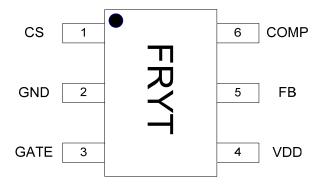




ORDERING INFORMATION

PART NUMBER	TEMPERATURE RANGE	PACKAGE	PINS	PACKING METHOD	OPTION (DC CORD %)	TOP MARK
ACT411US-T	-40°C to 85°C	SOT23-6	6	TUBE & REEL	3	FRYT

PIN CONFIGURATION



SOT23-6 ACT411US

PIN DESCRIPTIONS

PIN	NAME	DESCRIPTION
1	CS	Current Sense Pin. Connect an external resistor (R_{CS}) between this pin and ground to set peak current limit for the primary switch.
2	GND	Ground.
3	GATE	Gate Drive. Gate driver for the external MOSFET transistor.
4	VDD	Power Supply. This pin provides bias power for the IC during startup and steady state operation.
5	FB	Feedback Pin. Connect this pin to a resistor divider network from the auxiliary winding.
6	COMP	Compensation Pin.

- 2 -



ABSOLUTE MAXIMUM RATINGS®

PARAMETER	VALUE	UNIT
FB, CS, COMP to GND	-0.3 to + 6	V
VDD, GATE to GND	-0.3 to + 22	V
Maximum Power Dissipation (SOT23-6)	0.45	W
Operating Junction Temperature	-40 to 150	°C
Junction to Ambient Thermal Resistance (θ _{JA})	220	°C/W
Operating Junction Temperature	-40 to 150	°C
Storage Temperature	-55 to 150	°C
Lead Temperature (Soldering, 10 sec)	300	°C

①: Do not exceed these limits to prevent damage to the device. Exposure to absolute maximum rating conditions for long periods.

ELECTRICAL CHARACTERISTICS

 $(V_{DD}=13V,\,L_{M}=0.4\text{mH},\,R_{CS}=1.22\Omega,\,V_{OUT}=12V,\,N_{P}=79,\,N_{S}=13,\,N_{A}=14,\,T_{A}=25^{\circ}\text{C},\,\text{unless otherwise specified},\\ 12V1A\,\,\text{application})$

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Supply							
VDD Turn-On Voltage	V_{DDON}	V _{DD} Rising from 0V	11.11	12.35	13.58	V	
VDD Turn-Off Voltage	V_{DDOFF}	V _{DD} Falling after Turn-on	6.1	6.8	7.5	V	
VDD Over Voltage Protection	V_{DDOVP}	V _{DD} Rising from 0V	18.45	20.5	22.55	V	
Start Up Supply Current	I _{DDST}	V _{DD} = 11V, before VDD Turn-on		5	10	μA	
IDD Supply Current	I _{DD}	V _{DD} = 12V, after VDD Turn-on (no switching)		0.55	1	mA	
IDD Supply Current at Fault Mode	I _{DD}	V _{DD} = 12V, after VDD Turn-on, fault = 1		0.25		mA	
Feedback							
Effective FB Reference Voltage	V_{FBREF}		2.23	2.25	2.28	V	
ED Compling Planking Time	т	Light load	0.38	0.45	0.52	μs	
FB Sampling Blanking Time	T _{FB_BLK}	Heavy Load	1.1	1.3	1.5	μs	
Time needed for FB Sampling	_	FB sampling	0.5	0.65	0.75	μs	
(After blanking)	T_{FB_SAMP}	CC and Knee point detecting	0.22	0.25	0.29	μs	
FB Leakage Current	I _{BVFB}	V _{FB} = 3V			1	μA	
Current Limit							
CS Current Limit Threshold	V _{CSLIM}		0.99	1.00	1.01	٧	
CS Minimum Current Limits Threshold	V _{CSMIN}			300		mV	
CS to GATE Propagation Delay				60		ns	
Londing Edge Planking Time	Т	Light Load		150		ns	
Leading Edge Blanking Time	T _{CSBLANK}	Heavy Load		636		ns	



ELECTRICAL CHARACTERISTICS CONT'D

 $(V_{DD}=13V,L_{M}=0.4mH,R_{CS}=1.22\Omega,V_{OUT}=12V,N_{P}=79,N_{S}=13,N_{A}=14,T_{A}=25^{\circ}C,unless\ otherwise\ specified,12V1A\ application.)$

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
•					
DV _{COMP}	ACT411		3		%
T_{RISE}	VDD = 10V, CL = 1nF		150	250	ns
T_{FALL}	VDD = 10V, CL = 1nF		90		ns
R _{ONLO}	I _{SINK} = 30mA		10		Ω
R _{ONHI}	I _{SOURCE} = 30mA		31		Ω
	GATE = 18V, before VDD turn-on			1	μΑ
R _{COMP}	ACT411		0		kΩ
I _{COMP_SINK}	$V_{FB} = 3V$, $V_{COMP} = 2V$	15	40		μA
I _{COMP_SOUR}	V _{FB} = 1.5V, V _{COMP} = 2V	15	40		μΑ
Gm			71		μA/V
V_{COMPMAX}	V _{FB} = 1.5V		3.5		V
V_{COMPMIN}	V _{FB} = 3V		0.4		V
			2		V/V
			1		V/V
	COMP = 2.5V			1	μΑ
f _{MAX}		108	120	132	kHz
D_{MAX}		65	75		%
f _{MIN}			1164		Hz
	DVCOMP TRISE TFALL RONLO RONHI RCOMP ICOMP_SINK ICOMP_SOUR CE Gm VCOMPMAX VCOMPMIN fmax DMAX	DVcomp ACT411 TRISE VDD = 10V, CL = 1nF VDD = 10V, CL = 1nF RONLO ISINK = 30mA RONHI ISOURCE = 30mA GATE = 18V, before VDD turn-on CE GM VCOMPMAX VFB = 1.5V, VCOMP = 2V VCOMPMIN VFB = 3V VCOMPMIN VFB = 3V VCOMPMIN VFB = 3V COMP = 2V COMP = 2V COMPMIN VFB = 3V COMP = 2V COMPMIN VFB = 3V COMPMIN VFB = 3V COMPMIN VFB = 3V COMPMIN COMPMIN	DVCOMP ACT411	DVCOMP ACT411 3 3	DVcomp ACT411 3 3 3 3 3 3 3 3 3



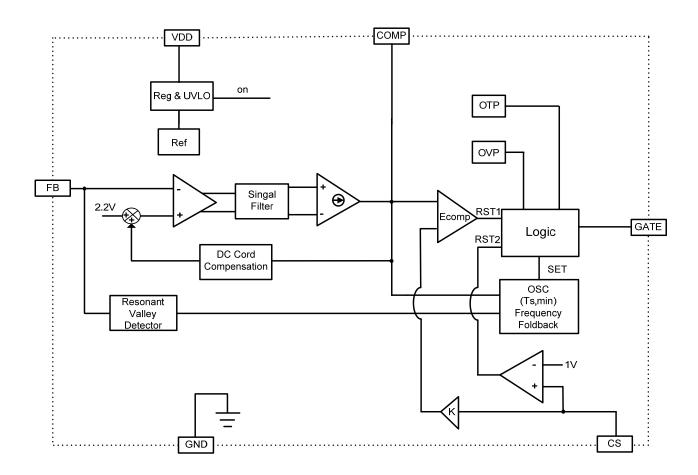
ELECTRICAL CHARACTERISTICS CONT'D

 $(V_{DD}=13V,\,L_{M}=0.4mH,\,R_{CS}=1.22\Omega,\,V_{OUT}=12V,\,N_{P}=79,\,N_{S}=13,\,N_{A}=14,\,T_{A}=25^{\circ}C,\,unless\,\,otherwise\,\,specified,12V1A\,\,application and the contraction of the contracti$

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Protection			•			•
CS Short Waiting Time			2	2.25	3	μs
CS Short Detection Threshold				0.1	0.15	V
CS Open Threshold Voltage				1.75		V
Abnormal OCP Blanking Time				190		ns
Inductance Short CS Threshold Voltage				1.75		V
Thermal Shutdown Temperature				135		°C
Thermal Hysteresis				20		°C
Line UVLO	I _{FBUVLO}			0.2		mA
Line UVLO Hysteresis				20		μΑ
Line OVP	I _{FBOVP}			2.4		mA
VFB Over Voltage Protection				3	_	V
Valley Detection		•	•			
Valley Detection Time Window		V _{COMP} = 0.45V		3.3		μs



FUNCTIONAL BLOCK DIAGRAM





FUNCTIONAL DESCRIPTION

ACT411 is a high performance peak current mode low-voltage PWM controller IC. The controller includes the most advance features that are required in the adaptor applications up to 36 Watt. Unique fast startup, frequency fold back, QR switching technique, accurate OLP, low standby mode operation, external compensation adjustment, short winding protection, OCP, OTP, OVP and UVLO are included in the controller.

Startup

Startup current of ACT411 is designed to be very low so that VDD could be charged to VDDON threshold level and device starts up quickly. A large value startup resistor can therefore be used to minimize the power loss yet reliable startup in application. For a typical AC/DC adaptor with universal input range design, two 1M Ω , 1/8 W startup resistors could be used together with a VDD capacitor(4.7uF) to provide a fast startup and yet low power dissipation design solution.

During startup period, the IC begins to operate with minimum lppk to minimize the switching stresses for the main switch, output diode and transformers. And then, the IC operates at maximum power output to achieve fast rise time. After this, V_{OUT} reaches about 90% V_{OUT} , the IC operates with a 'soft-landing' mode (decrease lppk) to avoid output overshoot.

Constant Voltage (CV) Mode Operation

In constant voltage operation, the ACT411 senses the output voltage at FB pin through a resistor divider network R5 and R6 in Figure 2. The signal at FB pin is pre-amplified against the internal reference voltage, and the secondary side output voltage is extracted based on Active-Semi's proprietary filter architecture.

This error signal is then amplified by the internal error amplifier. When the secondary output voltage is above regulation, the error amplifier output voltage decreases to reduce the switch current. When the secondary output voltage is below regulation, the error amplifier output voltage increases to ramp up the switch current to bring the secondary output back to regulation. The output regulation voltage is determined by the following relationship:

$$V_{OUTCV} = 2.20 V \times (1 + \frac{R_{FB1}}{R_{FB2}}) \times \frac{N_S}{N_A} - V_D$$
 (1)

where R_{FB1} (R5) and R_{FB2} (R6) are top and bottom feedback resistor, N_S and N_A are numbers of

transformer secondary and auxiliary turns, and V_{D} is the rectifier diode forward drop voltage at approximately 0.1A bias.

Constant Current (CC) Mode Operation

When the secondary output current reaches a level set by the internal current limiting circuit, the ACT411 enters current limit condition and causes the secondary output voltage to drop. As the output voltage decreases, so does the flyback voltage in a proportional manner. An internal current shaping circuitry adjusts the switching frequency based on the flyback voltage so that the transferred power remains proportional to the output voltage, resulting in a constant secondary side output current profile. The energy transferred to the output during each switching cycle is $\frac{1}{2}(LP \times ILIM^2) \times \eta$, where LP is the transformer primary inductance, ILIM is the primary peak current, and η is the conversion efficiency. From this formula, the constant output current can be derived:

$$I_{OUTCC} = \frac{1}{2} \times L_{p} \times \left(\frac{V_{CS}}{R_{CS}}\right)^{2} \times \left(\frac{\eta \times f_{SW}}{V_{OUTCV}}\right)$$
 (2)

where f_{SW} is the switching frequency and V_{OUTCV} is the nominal secondary output voltage. The constant current operation typically extends down to lower than 40% of nominal output voltage regulation.

Standby (No Load) Mode

In no load standby mode, the ACT411 oscillator frequency is further reduced to a minimum frequency while the current pulse is reduced to a minimum level to minimize standby power. The actual minimum switching frequency is programmable with an output preload resistor.

Loop Compensation

The ACT411 allows external loop compensation by connecting a capacitor to extend its applications, especially with different V_{OUT} in a wide output power range.

Primary Inductance Compensation

The ACT411 integrates a built-in primary inductance compensation circuit to maintain constant OLP despite variations in transformer manufacturing. The compensated ranges is +/-7%.

Primary Inductor Current Limit Compensation

The ACT411 integrates a primary inductor peak



FUNCTIONAL DESCRIPTION CONT'D

current limit compensation circuit to achieve constant OLP over wide line and wide load range.

Output Cable Resistance Compensation

The ACT411 provides internal programmable output cable resistance compensation during constant voltage regulation, monotonically adding an output voltage correction up to predetermined percentage at full power.

The feature allows better output voltage accuracy by compensating for the output voltage drop due to the output cable resistance.

Frequency Fold-back

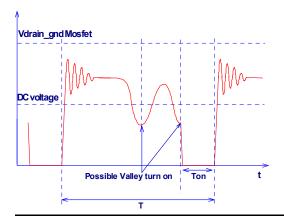
When the load drops to 75% of full load level, ACT411 starts to decrease the switching frequency, which is proportional to the load current ,to improve the efficiency of the converter as show in Functional Block Diagram.

This enables the application to meet all latest green energy standards. The actual minimum switching frequency is programmable with a small dummy load (while still meeting standby power).

Valley Switching

ACT411 employed valley switching from medium load to heavy load to reduce switching loss and EMI. After the switch is turned off, the ringing voltage from the auxiliary winding is applied to the VFB pin through feedback network R5, R6. Internally, the VFB pin is connected to an zero-crossing detector to generate the switch turn on signal when the conditions are met. In light load, the frequency fold back scheme starts to take control to determine the switch turn on signal, so thus the switching frequency.

Figure 1: Valley Switching at heavy load



Protection Features

The ACT411 provides full protection functions. The following table summarizes all protection functions.

PROTECTION FUNCTIONS		
V _{DD} Over Voltage	V _{DD} > 20.5V (4 duty cycle)	Auto Restart
VFB Over Voltage	V _{FB} > 3V (4 duty cycle)	Auto Restart
Over Temperature	T > 135°C	Auto Restart
Short Winding/ Short Diode	V _{CS} > 1.75V	Auto Restart
Over Load	IPK = I _{LIMIT}	Auto Restart
Output Short Circuit	V _{FB} < 0.56V	Auto Restart
Open Loop	No switching for 4 cycle	Auto Restart
V _{cc} Under Voltage	V _{CC} < 6.8V	Auto Restart

Auto-Restart Operation

ACT411 will enter auto-restart mode when a fault is identified. There is a startup phase in the auto-restart mode. After this startup phase the conditions are checked whether the failure is still present. Normal operation proceeds once the failure mode is removed. Otherwise, new startup phase will be initiated again.

To reduce the power loss during fault mode, the startup delay control is implemented. The startup delay time increases over lines.

Over Load Protection (OLP)

When the secondary output current reaches a level set by the internal current limiting circuit, the ACT411 enters current limit condition and causes the secondary output voltage to drop, the IC enters fault mode and enter auto restart mode.

ACT411 is able to achieve very accurate OLP (constant I_{OUT}) independent of input lines and primary inductor values.

Short Circuit Protection

When the secondary side output is short circuited, the ACT411 enters hiccup mode operation. This hiccup behavior continues until the short circuit is removed.



TYPICAL APPLICATION CONT'D

FB Over Voltage Protection

The ACT411 includes output over-voltage protection circuitry, which shuts down the IC when the output voltage is 40% above the normal regulation voltage 4 consecutive switching cycles. The ACT411 enters hiccup mode when an output over voltage fault is detected.

VDD Over Voltage Protection

ACT411 can monitor the converter output voltage. The voltage generated by the auxiliary winding tracks converter's output voltage through VDD, which is in proportion to the turn ratio ($V_{\text{OUT}}+V_{\text{DIODE}}$) xN_A/N_S. When the V_{OUT} is abnormally higher than design value for four consecutive cycles, IC will enter the restart process. A counter is used to reduce sensitivity to noise and prevent the auto start unnecessary.

Open Loop Protection

- 9 -

ACT411 is able to protect itself from damage when the control loop is open. The typical open loop condition includes either VFB floating or RFB5 open.

Over Temperature Shutdown

The thermal shutdown circuitry detects the ACT411 die temperature. The threshold is set at typical 135°C. When the die temperature rises above this threshold (135°C) the ACT411 is disabled and remains disabled until the die temperature falls below 115°C, at which point the ACT411 is reenabled.



TYPICAL APPLICATION CONT'D

Design Example

The design example below gives the procedure for a DCM fly back converter using an ACT411. Refer to Application Circuit Figure 2, the design for an adapter application starts with the following specification:

Input Voltage Range	90VAC - 265VAC, 50/60Hz
Output Power, Po	12W
Output Voltage, V _{OUTCV}	12V
Full Load Current, IOUTFL	1A
CC Current, I _{OUTMAX}	1.3-1.6A
System Efficiency CV, η	0.85

The operation for the circuit shown in Figure 1 is as follows: the rectifier bridge BD1 and the capacitor C1/C2 convert the AC line voltage to DC. This voltage supplies the primary winding of the transformer T1 and the startup resistor R7/R8 to VDD pin of ACT411 and C4. The primary power current path is formed by the transformer's primary winding, the mosfet, and the current sense resistor R9. The resistors R3, R2, diode D5 and capacitor C3 create a snubber clamping network that protects Q1 from voltage spike from the transformer primary leakage inductance. winding The network consisting of capacitor C4, diode D6 and resistor R4 provides a VDD supply voltage for ACT411 from the auxiliary winding of the transformer. The resistor R4 is optional, which filters out spikes and noise to makes VDD more stable. C4 is the decoupling capacitor of the supply voltage and energy storage component for startup. During power startup, the current charges C4 through startup resistor R7/R8 from the rectified high voltage. The diode D8 and the capacitor C5/C6 rectify filter the output voltage. The resistor divider consists of R5 and R6 programs the output voltage.

Since a bridge rectifier and bulk input capacitors are used, the resulting minimum and maximum DC input voltages can be calculated:

$$V_{INDC_MIN} = \sqrt{2V_{INAC_MIN}^2 - \frac{2P_{OUT}(\frac{1}{2f_L} - t_C)}{\eta \times C_{IN}}}$$

$$= \sqrt{2 \times 85^2 - \frac{2 \times 12 \times (\frac{1}{2 \times 47} - 3.5ms)}{0.85 \times 2 \times 10 \,\mu\text{F}}} \approx 115V$$
(3)

$$V_{IN(MAX)DC} = \sqrt{2} \times V_{IN(MAX)AC} = \sqrt{2} \times (265 V_{AC}) = 375 V$$
 (4)

Where η is the estimated circuit efficiency, f_L is the

line frequency, t_{C} is the estimated rectifier conduction time, C_{IN} is empirically selected to be $2x10\mu F$ electrolytic capacitors.

The maximum duty cycle is set to be 45% at low line voltage 85VAC and the circuit efficiency is estimated to be 85%. Then the maximum average input current is:

$$I_{IN_MAX} = \frac{V_{OUT} \times I_{OUT_CC}}{V_{INDC_MIN} \times \eta}$$

$$= \frac{12 \times 1.6}{115 \times 0.85} = 196 \text{ mA}$$
(5)

The maximum input primary peak current:

$$I_{LIM} = \frac{2 \times L_{IN}}{D_{MAX}} = \frac{2 \times 196}{0.45} = 873 \, \text{mA}$$
 (6)

The primary inductance of the transformer:

$$L_{p} = \frac{V_{INDC_MIN} D_{max}}{I_{LIM} \times f_{s}}$$

$$= \frac{115 \times 0.45}{873 \text{ mA} \times 110 \text{ k}} \approx 0.4 \text{ mH}$$
(7)

The maximum primary turns on time:

$$T_{ON_MAX} = L_p \frac{I_{LIM}}{V_{INDC_MIN}}$$

$$= \frac{0.4 \text{ mH} \times 873 \text{ mA}}{115} = 3.04 \,\mu\text{s}$$
(8)

The ringing periods from primary inductance with mosfet Drain-Source capacitor:

$$T_{RINGING_MAX} = 2\pi \sqrt{L_{p_MAX}} C_{DS_MAX}$$

= $2 \times 3.14 \times \sqrt{0.4mH} \times (1 + 7\%) \times 100PF = 1.3 \mu s$ (9)

Design only an half ringing cycle at maximum load in minimum low line, so secondly reset time:

$$T_{RST} = T_{SW} - T_{ON_MAX} - 0.5T_{RINGING_MAX}$$

= 1/110kHz - 3.04\mus - 0.5\times 1.3\mus = 5.4\mus

Base on conservation of energy and transformer transform identity, the primary to secondary turns ratio N_P/N_S :

$$\frac{N_P}{N_S} = \frac{T_{ON}}{T_{RST}} \times \frac{V_{IN_MIN}}{V_{OUT} + V_D}$$

$$= \frac{3.03}{5.4} \times \frac{115}{12 + 0.45} = 5.18$$
(11)

The auxiliary to secondary turns ratio N_A/N_S:

$$\frac{N_A}{N_S} = \frac{V_{DD} + V_D'}{V_{OUT} + V_D} = \frac{13 + 0.45}{12 + 0.45} = 1.08$$
 (12)



TYPICAL APPLICATION CONT'D

An EE16 core is selected for the transformer. From the manufacture's catalogue recommendation, the gapped core with an effective inductance A_{LE} of 65 nH/T² is selected. The turn of the primary winding is:

$$N_P = \sqrt{\frac{L_P}{A_{LE}}} = \sqrt{\frac{0.4 \, mH}{65 \, nH \, / \, T^2}} = 78 \, T$$
 (13)

The turns of secondary and auxiliary winding can be derived accordingly:

$$N_{\rm S} = \frac{N_{\rm s}}{N_{\rm p}} \times N_{\rm p} = \frac{1}{5.18} \times 78 \approx 13T$$
 (14)

$$N_A = \frac{N_A}{N_S} \times N_S = 1.08 \times 13 = 14T$$
 (15)

Determining the value of the current sense resistor (R9) uses the peak current in the design. Since the ACT411 internal current limit is set to 1V, the design of the current sense resistor is given by:

$$R_{CS} = \frac{V_{CS}}{\sqrt{\frac{2 \times I_{OUT} _{OCP} \times V_{OUT}}{L_P \times F_{SW} \times \eta_{system}}}}$$

$$= \frac{1}{\sqrt{\frac{2 \times 1.6 \times 12}{0.4 \text{ mH} \times 110 \text{ kHz} \times 0.85}}} \approx 1.24.\Omega$$
(16)

The voltage feedback resistors are selected according to the loccmax and Vo. The design lo_cc max is given by:

$$f_{s} = \frac{N_{p}}{N_{s}} \times \frac{R_{fb1} \times R_{fb2}}{R_{fb1} + R_{fb2}} \times \frac{V_{O} + V_{D}}{L_{p} \times \frac{V_{Cs}}{R_{cs}} \times K_{f_{SW}}}$$
(17)

The design Vo is given by:

$$V_{o} = (1 + \frac{R_{fb1}}{R_{fb2}}) \times \frac{N_{s}}{N_{a}} \times V_{FB} - V_{D}$$
 (18)

Where k is IC constant and K=0.000075, then we can get the value:

$$R_{\text{fb1}} = 53.6K, R_{\text{fb2}} = 10.2K$$
 (19)

When selecting the output capacitor, a low ESR electrolytic capacitor is recommended to minimize ripple from the current ripple. The approximate equation for the output capacitance value is given by:

$$C_{OUT} = \frac{I_{OUT}}{f_{sw} \times V_{gipple}} = \frac{1}{110 \text{ k} \times 50 \text{ mV}} = 182 \mu\text{F}$$
 (20)

Two $470\mu F$ electrolytic capacitors are used to keep the ripple small.

PCB Layout Guideline

Good PCB layout is critical to have optimal performance. Decoupling capacitor (C4) and feedback resistor (R5/R6) should be placed close to VDD and FB pin respectively. There are two main power path loops. One is formed by C1/C2, primary winding, Mosfet transistor and current sense resistor (R9). The other is secondary winding, rectifier D8 and output capacitors (C5/C6). Keep these loop areas as small as possible. Connecting high current ground returns, the input capacitor ground lead, and the ACT411 GND pin to a single point (star ground configuration).



Figure 2: ACT411, Universal VAC Input, 12V/1A Output Charger

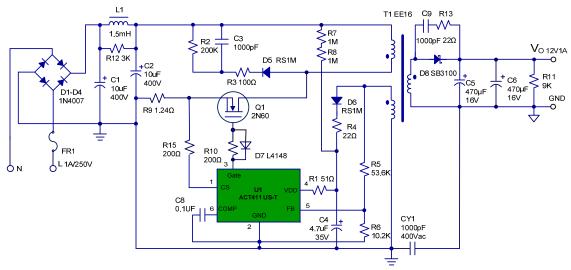


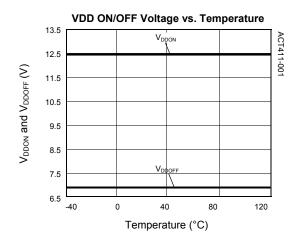
Table 2:

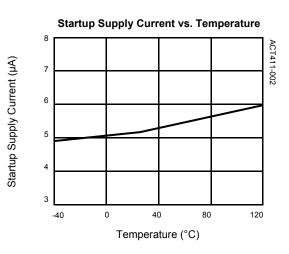
ACT411 Bill of Materials

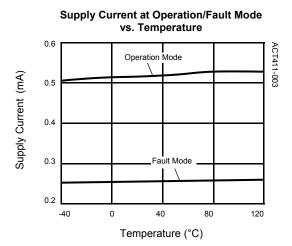
ITEM	REFERENCE	DESCRIPTION	QTY	MANUFACTURER
1	U1	IC, ACT411,SOT23-6	1	Active-Semi.
2	C1,C2	Capacitor, Electrolytic, 10µF/400V, 10x15mm	2	KSC
3	C3	Capacitor, Ceramic, 1000pF/500V, 0805,SMD	1	POE
4	C4	Capacitor, Electrolytic,10µF/35V,5x11mm	1	KSC
5	C5,C6	Capacitor, Electrolytic, 470µF/16V, 8x11.5mm	2	KSC
6	C8	Capacitor, Ceramic, 0.1µF/25V, 0805,SMD	1	POE
7	C9	Capacitor, Ceramic, 1000pF/100V, 0805,SMD	1	POE
8	CY1	Safety Y1,Capacitor,1000pF/400V,Dip	1	UXT
9	D1-D4	Diode,Rectifier,1000V/1A,1N4007, DO-41	4	Good-Ark
10	D5	Fast Recovery Rectifier, RS1M,1000V/1.0A, RMA	1	PANJIT
11	D6	Fast Recovery Rectifier,RS1D,200V/1.0A,SMA	1	PANJIT
12	D7	Diode, 1N4148 SMD	1	PANJIT
13	D8	Diode, schottky, 100V/5A, SB5100, DO-47	1	Good-Ark
14	L1	Axial Inductor, 1.5mH, 5*7,Dip	1	SoKa
15	L2	Axial Inductor, 0.55*5T, 5*7,Dip	1	SoKa
16	Q1	Mosfet Transistor, 4N60,TO-220	1	Infineon
17	PCB1	PCB, L*W*T=52.2x30x1.6mm,Cem-1,Rev:A	1	Jintong
18	FR1	Fuse,1A/250V	1	TY-OHM
19	R2	Carbon Resistor, 200KΩ, 1206, 5%	1	TY-OHM
20	R3	Chip Resistor, 100Ω , 0805 , 5%	1	TY-OHM
21	R1	Chip Resistor, 51Ω, 0805, 5%	1	TY-OHM
22	R4,R13	Chip Resistor, 22Ω, 0805, 5%	2	TY-OHM
23	R5	Chip Resistor, 53.6KΩ, 0805,1%	1	TY-OHM
24	R6	Chip Resistor, 10.2KΩ, 0805, 1%	1	TY-OHM
25	R7,R8	Chip Resistor, $1M\Omega$, 0805 , 5%	2	TY-OHM
26	R9	Chip Resistor, 1.24Ω, 1206,1%	1	TY-OHM
27	R10,R15	Chip Resistor, 200Ω, 0805 , 5%	2	TY-OHM
28	R11	Chip Resistor, 7KΩ, 0805, 5%	1	TY-OHM
29	R12	Chip Resistor, 3KΩ, 0805 , 5%	1	TY-OHM
30	T1	Transformer, Lp=0.4mH, EE16	1	

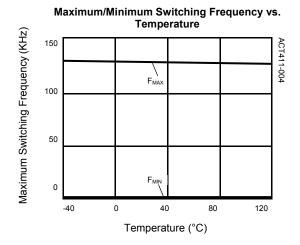


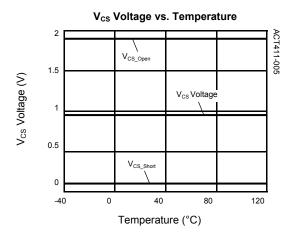
TYPICAL PERFORMANCE CHARACTERISTICS

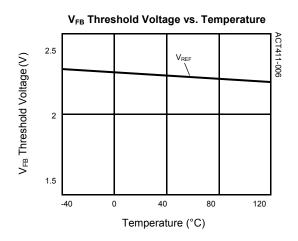






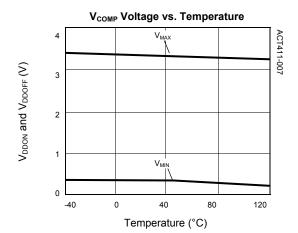








TYPICAL PERFORMANCE CHARACTERISTICS

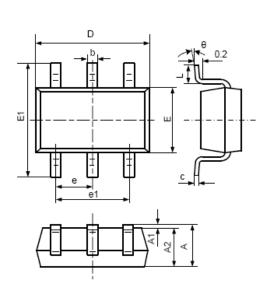


- 14 -



PACKAGE OUTLINE

SOT23-6 PACKAGE OUTLINE AND DIMENSIONS



SYMBOL		DIMENSION IN MILLIMETERS		SION IN HES
	MIN	MAX	MIN	MAX
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
Е	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950 TYP		0.037	TYP
e1	1.800	2.000	0.071	0.079
L	0.700	REF	0.028 REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Active-Semi, Inc. reserves the right to modify the circuitry or specifications without notice. Users should evaluate each product to make sure that it is suitable for their applications. Active-Semi products are not intended or authorized for use as critical components in life-support devices or systems. Active-Semi, Inc. does not assume any liability arising out of the use of any product or circuit described in this datasheet, nor does it convey any patent license.

Active-Semi and its logo are trademarks of Active-Semi, Inc. For more information on this and other products, contact <u>sales@active-semi.com</u> or visit <u>http://www.active-semi.com</u>.

◆ active-semi is a registered trademark of Active-Semi.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Power Management IC Development Tools category:

Click to view products by Active-Semi manufacturer:

Other Similar products are found below:

EVAL-ADM1168LQEBZ EVB-EP5348UI MIC23451-AAAYFL EV MIC5281YMME EV DA9063-EVAL ADP122-3.3-EVALZ ADP1300.8-EVALZ ADP130-1.2-EVALZ ADP130-1.5-EVALZ ADP130-1.8-EVALZ ADP1714-3.3-EVALZ ADP1716-2.5-EVALZ ADP1740-1.5EVALZ ADP1752-1.5-EVALZ ADP1828LC-EVALZ ADP1870-0.3-EVALZ ADP1871-0.6-EVALZ ADP1873-0.6-EVALZ ADP1874-0.3EVALZ ADP1882-1.0-EVALZ ADP199CB-EVALZ ADP2102-1.25-EVALZ ADP2102-1.875EVALZ ADP2102-1.8-EVALZ ADP2102-2EVALZ ADP2102-3-EVALZ ADP2102-4-EVALZ ADP2106-1.8-EVALZ ADP2147CB-110EVALZ AS3606-DB BQ24010EVM
BQ24075TEVM BQ24155EVM BQ24157EVM-697 BQ24160EVM-742 BQ24296MEVM-655 BQ25010EVM BQ3055EVM

NCV891330PD50GEVB ISLUSBI2CKIT1Z LM2744EVAL LM2854EVAL LM3658SD-AEV/NOPB LM3658SDEV/NOPB LM3691TL1.8EV/NOPB LM4510SDEV/NOPB LM5033SD-EVAL LP38512TS-1.8EV EVAL-ADM1186-1MBZ EVAL-ADM1186-2MBZ